GM4403

PNP EPITAXIAL PLANAR TRANSISTOR

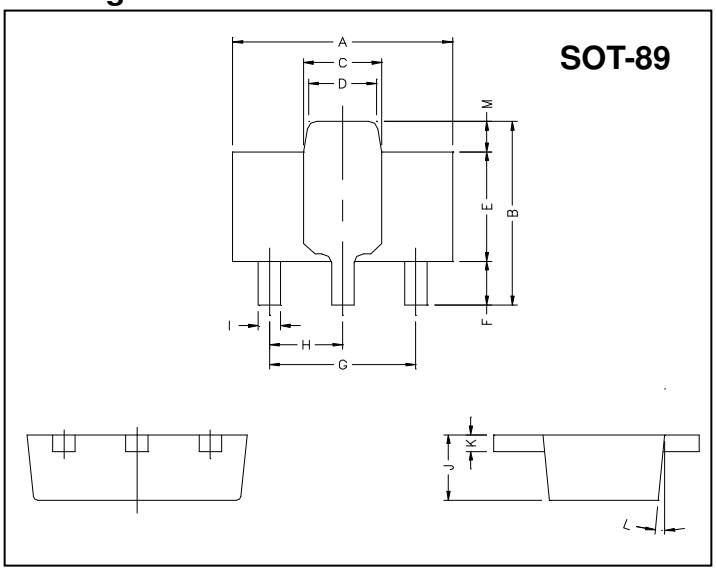
Description

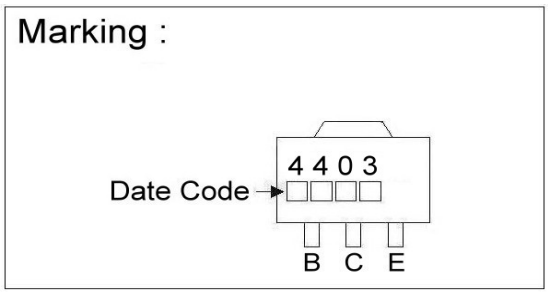
The GM4403 is designed for general purpose switching and amplifier applications.

Features

- Complementary to GM4401
- High Power Dissipation: 1W at 25℃
- High DC Current Gain: 100-300 at 150mA

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00 REF.	
B	4.05	4.25	H	1.50 REF.	
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage at Ta=25℃	VCBO	-40	V
Collector to Emitter Voltage at Ta=25℃	VCEO	-40	V
Emitter to Base Voltage at Ta=25℃	VEBO	-5	V
Collector Current at Ta=25℃	IC	-600	mA
Total Power Dissipation at Ta=25℃	PD	1	W

Characteristics at Ta = 25℃

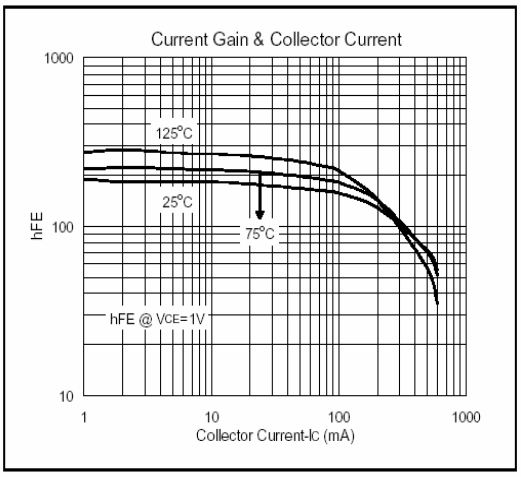
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-40	-	-	V	I_C=-100uA
BV_{CEO}	-40	-	-	V	I_C=-1mA
BV_{EBO}	-5	-	-	V	I_E=-10uA
I_{CEX}	-	-	-100	nA	V_{CE}=-35V, V_{BE}=-0.4V
*V_{CE}(sat)1	-	-	-400	mV	I_C=-150mA, I_B=-15mA
*V_{CE}(sat)2	-	-	-750	mV	I_C=-500mA, I_B=-50mA
*V_{BE}(sat)1	-750	-	-950	mV	I_C=-150mA, I_B=-15mA
*V_{BE}(sat)2	-	-	-1.3	V	I_C=-500mA, I_B=-50Ma
*h_{FE}1	30	-	-		V_{CE}=-1V, I_C=-0.1mA
*h_{FE}2	60	-	-		V_{CE}=-1V, I_C=-1mA
*h_{FE}3	100	-	-		V_{CE}=-1V, I_C=-10mA
*h_{FE}4	100	-	300		V_{CE}=-2V, I_C=-150mA
*h_{FE}5	20	-	-		V_{CE}=-2V, I_C=-500mA
fT	200	-	-	MHz	V_{CE}=-10V, I_C=-20mA, f=100MHz
Cob	-	-	8.5	pF	V_{CE}=-10V, f=1MHz

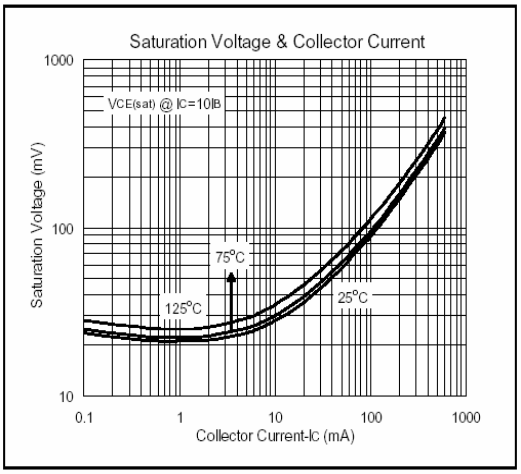
Classification Of h_{FE}4

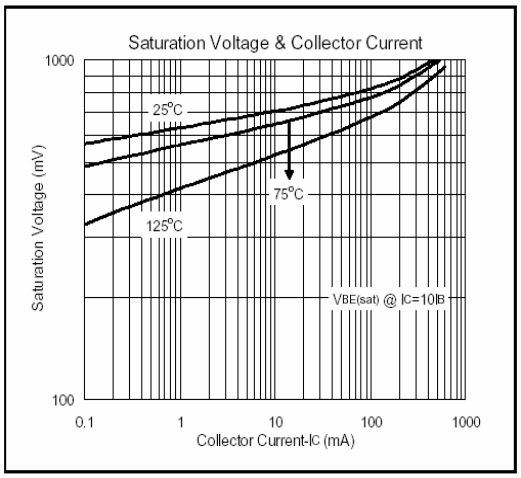
Rank	A	B
Range	100-210	190-300

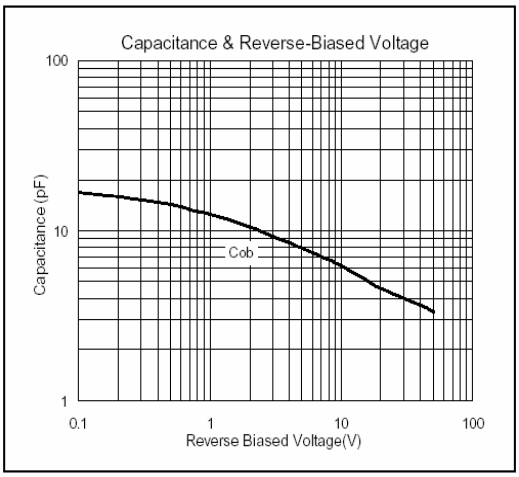
*** Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%**

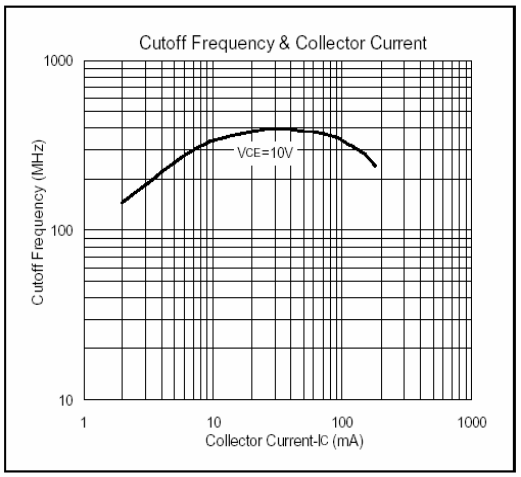
Characteristics Curve

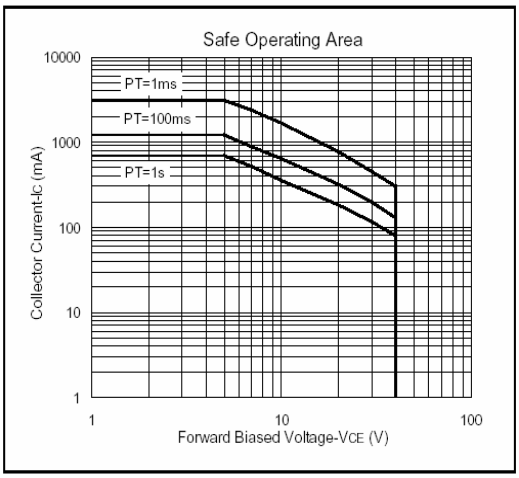












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